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(54) **SEMICONDUCTOR STRUCTURE
MANUFACTURING METHOD AND
SEMICONDUCTOR STRUCTURE**

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(57) **ABSTRACT**

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A semiconductor structure manufacturing method includes: providing a substrate and forming a groove in the substrate; forming a barrier layer on a sidewall of the groove; epitaxially growing a channel material from a bottom of the groove to form an intermediate structure in the groove; and removing a portion of the intermediate structure and a portion of the substrate to form a fin structure.

Related U.S. Application Data

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